

TAIWAN SEMICONDUCTOR RoHS —

Single Phase 10.0 AMPS. Glass Passivated Bridge Rectifiers



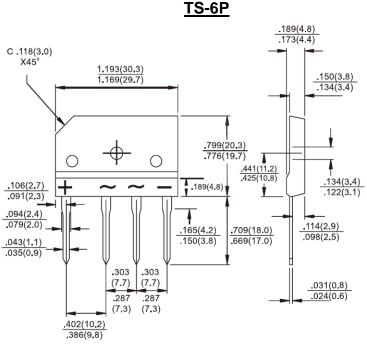


Features

- ♦ UL Recoganized File # E-326243
- ♦ Glass passivated junction
- ♦ Ideal for printed circuit board
- ♦ High case dielectric strength of 2000V_{RMS}
- Plastic material has Underwriters Laboratory Flammability Classification 94V-0
- ♦ Typical IR less than 0.1uA
- ♦ High surge current capability to 200A
- ↔ High temperature soldering guaranteed:
 260 °C / 10 seconds at 5 lbs.,(2.3kg) tension
- ♦ Green compound with suffix "G" on packing code & prefix "G" on datecode.

Mechanical Data

- ♦ Case: Molded plastic body
- Terminals: Pure tin plated, Lead free, Leads solderable per MIL-STD-202, Method 208
- ♦ Weight: 7.15 grams
- ♦ Mounting torque : 8.17 in-lbs Max.



Dimensions in inches and (millimeters)

Marking Diagram

TS10P0XG

G

Y

WW

- TS10P0XG
- = Specific Device Code
 - = Green Compound
 - = Year
 - = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 $^\circ\!\mathrm{C}$ ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

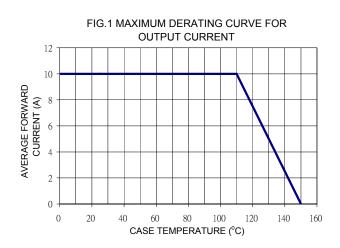
Type Number TS10P	TS10P 06G	TS10P 07G	Units
virginity virginity <thvirginity< th=""> virginity <thvirginity< th=""> virginity <thvirginity< th=""> <thvirginity< th=""> <thvir< td=""><td>800</td><td>1000</td><td>V</td></thvir<></thvirginity<></thvirginity<></thvirginity<></thvirginity<>	800	1000	V
Voltage V _{RMS} 35 70 140 280 420	560	700	V
locking Voltage V _{DC} 50 100 200 400 600	800	1000	V
age Forward Rectified Current I _{F(AV)} 10			А
Surge Current, 8.3 ms Single Half Sine- osed on Rated Load (JEDEC method)			А
(t < 8.3mS) ² t 166			A ² S
ntaneous Forward Voltage (Note 1) @ 5 A V _F 1.0 @10 A 1.1			V
Reverse Current@ $T_A = 25 \degree C$ 10bocking Voltage@ $T_A = 125 \degree C$ IR500			uA uA
n Capacitance Per Leg (Note 2) Cj 77			pF
I Resistance R _{eJC} 1.4			^o C/W
perature Range T _J - 55 to + 150			°C
rature Range T _{STG} - 55 to + 150			°C
berature Range $T_{\rm J}$ - 55 to + 150			

Note 1 : Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2 : Measured at 1MHz and applied Reverse bias of 4.0V DC.



RATINGS AND CHARACTERISTIC CURVES (TS10P01G THRU TS10P07G)





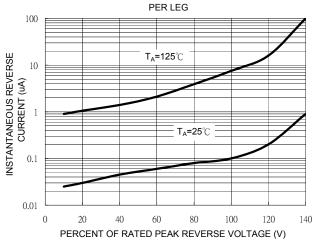
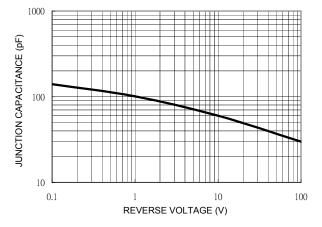


FIG. 5 TYPICAL JUNCTION CAPACITANCE



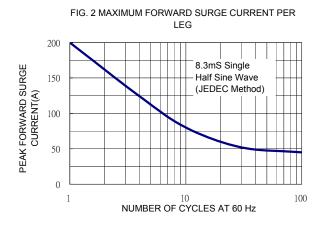


FIG. 4 TYPICAL FORWARD CHARACTERISRICS

